

+2.7V, Single-Supply, Cellular-Band **Linear Power Amplifiers**

General Description

The MAX2267/MAX2268/MAX2269 power amplifiers are optimized for IS-98-based CDMA and PDC cellular telephones operating in the Japanese cellular-frequency band. When matched for CDMA operation, the amplifiers achieve 27dBm output power with 35% efficiency (MAX2268), with margin over the adjacent and alternate channel specification. At a +17dBm output—a very common power level for CDMA phones—the MAX2268 still has 7% efficiency, yielding excellent overall talk time. At the same power level, the MAX2267/MAX2269 have an unprecedented 12%/17% efficiency, while still obtaining 28%/29% efficiency at maximum output power.

The MAX2267/MAX2268/MAX2269 have internally referenced bias ports that are normally terminated with simple resistors. The bias ports allow customization of ACPR margin and gain. They can also be used to "throttle back" bias current when generating low power levels. The MAX2267/MAX2268/MAX2269 have excellent gain stability over temperature (±0.8dB), so overdesign of driver stages and excess driver current are dramatically reduced, further increasing the phone's talk time. The devices can be operated from +2.7V to +4.5V while meeting all ACPR specifications over the entire temperature range.

The devices are packaged in a 16-pin TSSOP with exposed paddle (EP). For module or direct chip attach applications, the MAX2267 is also available in die form.

Applications

Cellular-Band CDMA Phones Cellular-Band PDC Phones 2-Way Pagers Power-Amplifier Modules

Selector Guide

	HIGH POWER-ADDED EFFICIENCY (%)						
DEVICE	CDMA AT +27dBm	CDMA AT +17dBm	PDC AT +29dBm				
MAX2267	28	12	_				
MAX2268	34	7	41				
MAX2269	29	17	_				

Features

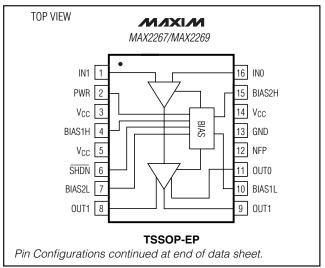
- **♦ Low Average CDMA Current Consumption in Typical Urban Scenario** 55mA (MAX2267) 90mA (MAX2268) 50mA (MAX2269)
- ♦ 0.5µA Shutdown Mode Eliminates External **Supply Switch**
- ♦ ±0.8dB Gain Variation Over Temperature
- ♦ No External Reference or Logic Interface **Circuitry Needed**
- ♦ Supply Current and ACPR Margin Dynamically **Adjustable**
- ♦ +2.7V to +4.5V Single-Supply Operation
- ♦ 35% Efficiency at +2.7V Operation

Ordering Information

PART	TEMP. RANGE	RANGE PACKAGE	
MAX2267EUE	-40°C to +85°C	16 TSSOP-EP	
MAX2267E/D	-40°C to +85°C	Dice*	
MAX2268EUE	-40°C to +85°C	16 TSSOP-EP	TSSOP-EP 5mm x 6.4mm
MAX2269EUE	-40°C to +85°C	16 TSSOP-EP	

^{*}Contact factory for dice specifications.

Pin Configurations/ **Functional Diagrams**



MIXIM

Maxim Integrated Products 1

ABSOLUTE MAXIMUM RATINGS

V _{CC} to GND (no RF input)	0.3V to +5V
Logic Inputs to GND	0.3V to (V _{CC} + 0.3V)
BIAS_ to GND	0.3V to $(V_{CC} + 0.3V)$
RF Input Power	+6dBm (20mW)
Logic Input Current	±10mA
Output VSWR with +6dBm Input	2.5:1

Total DC Power Dissipation (TPADDLE = +	-100°C)
16-Pin TSSOP-EP (derate 60mW/°C	
above T _{PADDLE} = +100°C)	4W
hetaJA	8°C/W
Operating Temperature Range	40°C to +85°C
Junction Temperature	+150°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (soldering, 10s)	+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

 $(V_{CC} = +2.7 \text{V to } +4.5 \text{V no input signal applied}, V_{\overline{SHDN}} = 2.0 \text{V}, T_A = T_{MIN} \text{ to } T_{MAX}, \text{ unless otherwise noted}.$ Typical values are at $V_{CC} = +3.5 \text{V}$ and $T_A = +25 ^{\circ}\text{C}$.) (Note 8)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS
Operating Voltage Range	Vcc			2.7		4.5	V
		MAX2267/MAX2269	PWR = V _{CC}		100		
Idle Current	Icc	IVIAAZZ07/IVIAAZZ09	PWR = GND		34		mA
		MAX2268			90		
Shutdown Supply Current	Icc	SHDN = PWR = GND			0.5	10	μΑ
Logic Input Current High		Logic = V _{CC}		-1		5	μΑ
Logic Input Current Low		Logic = GND		-1		1	μΑ
Logic Threshold High				2.0			V
Logic Threshold Low						0.8	V

AC ELECTRICAL CHARACTERISTICS—MAX2267

(MAX2267 EV kit, $V_{CC} = V_{PWR} = V_{\overline{SHDN}} = +3.5V$, $f_{IN} = 906MHz$, CDMA modulation, $\overline{SHDN} = V_{CC}$, matching networks tuned for 887MHz to 925MHz operation, 50Ω system, $T_A = +25^{\circ}C$, unless otherwise noted.)

PARAMETER	SYMBOL	COND	ITIONS	MIN	TYP	MAX	UNITS
Frequency Range (Notes 1, 2)	fIN	PWR = V _{CC} or GND		887		925	MHz
		T _A = +25°C		24.5	26		
Power Gain (Note 1)	GP	TA = TMIN to TMAX		23			dB
		PWR = GND		20.5	23		
Gain Variation vs. Temperature (Note 1)		$T_A = T_{MIN}$ to T_{MAX} , relative to $T_A = +25$ °C			±0.8		dB
Output Power	Pout	ACPR specification met with	PWR = V _{CC}	27			dBm
(High-Power Mode) (Note 1)		$f_{IN} = 887MHz$ to $925MHz$	$PWR = V_{CC} = 2.8V$	24.5	25.5		dbiii
		ACPR specification	PWR = GND	16	17.5		
Output Power (Low-Power Mode) (Note 1)	Pout	met with f _{IN} = 887MHz to 925MHz	PWR = GND, V _{CC} = 2.8V	14	15.5		dBm

AC ELECTRICAL CHARACTERISTICS—MAX2267 (continued)

(MAX2267 EV kit, $V_{CC} = V_{PWR} = V_{\overline{SHDN}} = +3.5V$, $f_{IN} = 906 MHz$, CDMA modulation, $\overline{SHDN} = V_{CC}$, matching networks tuned for 887MHz to 925MHz operation, 50Ω system, $T_A = +25^{\circ}C$, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Adjacent-Channel Power Ratio Limit (Notes 1, 2)	ACPR	V _{CC} = 2.8V to 4.5V, offset = 885kHz, 30kHz BW, f _{IN} = 887MHz to 925MHz	-44	-48		dBc
Alternate-Channel Power Ratio Limit (Notes 1, 2)	ACPR	V _{CC} = 2.8V to 4.5V, offset = 1980kHz, 30kHz BW, f _{IN} = 887MHz to 925MHz	-56	-57.5		dBc
Power-Added Efficiency	PAE	$PWR = V_{CC}, P_{OUT} = +27dBm$		28		%
(Note 3)	FAL	PWR = GND, P _{OUT} = 17.5dBm		12		/0
Power-Mode Switching Time		(Note 4)		550		ns
Turn-On Time (Notes 1, 4)		PWR = V _{CC} or GND		1	5	μs
Maximum Input VSWR	VSWR	$f_{IN} = 887MHz$ to 925MHz, PWR = GND or V _{CC}		2.3:1		
Nonharmonic Spurious due to Load Mismatch (Notes 1, 5)		P _{IN} = +6dBm			-60	dBc
Noise Power (Note 6)		Measured at 851MHz		-137		dBm/Hz
INDISE I OWEI (INDIE 0)		PWR = GND, measured at 851MHz		-134		שווווטון
Harmonic Suppression		(Note 7)		32		dBc

AC ELECTRICAL CHARACTERISTICS—MAX2268

(MAX2268 EV kit, $V_{CC} = V_{\overline{SHDN}} = +3.5V$, $f_{IN} = 906MHz$, CDMA modulation, matching networks tuned for 887MHz to 925MHz operation, 50Ω system, $T_A = +25^{\circ}C$, unless otherwise noted.)

PARAMETER	SYMBOL	CONE	OITIONS	MIN	TYP	MAX	UNITS
Frequency Range (Notes 1, 2)	fIN			887		925	MHz
Power Gain (Note 1)	G _P	T _A = +25°C		25.5	27		dB
rower Gain (Note 1)	GP GP	$T_A = T_{MIN}$ to T_{MAX}		24			ub
Gain Variation vs. Temperature (Note 1)		T _A = T _{MIN} to T _{MAX} , re	$T_A = T_{MIN}$ to T_{MAX} , relative to $T_A = +25$ °C		±0.7		dB
Output Power (Note 1)	Pout	ACPR specification met with	V _{CC} = 3.5V	27			dBm
output Fower (Note 1)	1 001	f _{IN} = 887MHz to 925MHz	V _{CC} = 2.8V	24.5	25.5		dbiii
Adjacent-Channel Power Ratio (Notes 1, 2)	ACPR		V _{CC} = 2.8V to 4.5V, offset = 885kHz, 30kHz BW, f _{IN} = 887MHz to 925MHz		-48		dBc
Alternate-Channel Power Ratio (Notes 1, 2)	ACPR		V _{CC} = 2.8V to 4.5V, offset = 1980kHz, 30kHz BW, f _{IN} = 887MHz to 925MHz		-57.5		dBc
Power-Added Efficiency	PAE	P _{IN} adjusted to give P	OUT = 27dBm		35		%
(Note 3)	FAL	P _{IN} adjusted for P _{OUT} = 13.6dBm			5.5		/^
Turn-On Time (Notes 1, 4)					1	5	μs
Maximum Input VSWR	VSWR	f _{IN} = 887MHz to 925M	f _{IN} = 887MHz to 925MHz		1.5:1		

AC ELECTRICAL CHARACTERISTICS—MAX2268 (continued)

(MAX2268 EV kit, $V_{CC} = V_{\overline{SHDN}} = +3.5V$, $f_{IN} = 906MHz$, CDMA modulation, matching networks tuned for 887MHz to 925MHz operation, 50Ω system, $T_A = +25^{\circ}C$, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Nonharmonic Spurious Due to Load Mismatch (Notes 1, 5)		$P_{IN} = +6dBm$			-60	dBc
Noise Power (Note 6)		Measured at 851MHz		-138		dBm/Hz
Harmonic Suppression		(Note 7)		47		dBc

AC ELECTRICAL CHARACTERISTICS—MAX2269

(MAX2269 EV kit, $V_{CC} = V_{PWR} = V_{\overline{SHDN}} = +3.5V$, $f_{IN} = 906MHz$, CDMA modulation, $\overline{SHDN} = V_{CC}$, matching networks tuned for 887MHz to 925MHz operation, 50Ω system, $T_A = +25^{\circ}C$, unless otherwise noted.)

PARAMETER	SYMBOL	COND	ITIONS	MIN	TYP	MAX	UNITS
Frequency Range (Notes 1, 2)	fIN	PWR = V _{CC} or GND		887		925	MHz
		T _A = +25°C		24.5	26		
Power Gain (Note 1)	GP	TA = TMIN to TMAX		23			dB
		PWR = GND		23.5	26		
Gain Variation vs. Temperature (Note 1)		$T_A = T_{MIN}$ to T_{MAX} , relative to $T_A = +25$ °C			±0.8		dB
Output Power	Pout	ACPR specification met with	PWR = V _{CC}	27			dBm
(High-Power Mode) (Note 1)	1 001	$f_{IN} = 887MHz$ to $925MHz$	$PWR = V_{CC} = 2.8V$	24.5	25.5		dBiii
		ACPR specification	PWR = GND	15.5	17		
Output Power (Low-Power Mode) (Note 1)	Pout	met with $f_{IN} = 887MHz$ to $925MHz$	PWR = GND, V _{CC} = 2.8V	13.5	15		dBm
Adjacent-Channel Power Ratio Limit (Notes 1, 2)	ACPR	V _{CC} = 2.8V to 4.5V, offset = 885kHz, 30kHz BW, f _{IN} = 887MHz to 925MHz		-44	-48		dBc
Alternate-Channel Power Ratio Limit (Notes 1, 2)	ACPR	V _{CC} = 2.8V to 4.5V, offset = 1980kHz, 30kHz BW, f _{IN} = 887MHz to 925MHz		-56	-57.5		dBc
Power-Added Efficiency	PAE	PWR = V _{CC} , P _{OUT} = +			29		%
(Note 3)	'/\L	PWR = GND, Pout =	17dBm		17		/0

AC ELECTRICAL CHARACTERISTICS—MAX2269 (continued)

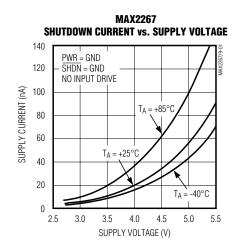
(MAX2269 EV kit, $V_{CC} = V_{PWR} = V_{\overline{SHDN}} = +3.5V$, $f_{IN} = 906MHz$, CDMA modulation, $\overline{SHDN} = V_{CC}$, matching networks tuned for 887MHz to 925MHz operation, 50Ω system, $T_A = +25^{\circ}C$, unless otherwise noted.)

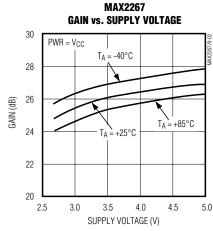
PARAMETER	SYMBOL	CONDITIONS		TYP	MAX	UNITS
Power-Mode Switching Time		(Note 4)		550		ns
Turn-On Time (Notes 1, 4)		PWR = V _{CC} or GND		1	5	μs
Maximum Input VSWR	VSWR	f_{IN} = 887MHz to 925MHz, PWR = GND or V _{CC}		2.4:1		
Nonharmonic Spurious due to Load Mismatch (Notes 1, 5)		P _{IN} = +6dBm			-60	dBc
Noise Power (Note 6)		Measured at 851MHz		-137		dBm/Hz
Noise Fower (Note 6)		PWR = GND, measured at 851MHz		-130		UDITI/T IZ
Harmonic Suppression		(Note 7)		32		dBc

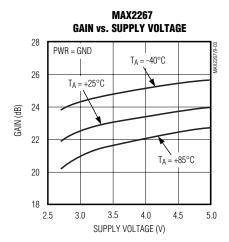
- Note 1: Minimum and maximum values are guaranteed by design and characterization, not production tested.
- **Note 2:** P_{MAX} is met over this frequency range at the ACPR limit with a single matching network. For optimum performance at other frequencies, the output matching network must be properly designed. See the *Applications Information* section. Operation between 750MHz and 1000MHz is possible but has not been characterized.
- **Note 3:** PAE is specified into a 50Ω load, while meeting the ACPR requirement.
- Note 4: Time from logic transition until POUT is within 1dB of its final mean power.
- Note 5: Murata isolator as load with 20:1 VSWR any phase angle after isolator.
- Note 6: Noise power can be improved by using the circuit in Figures 1 and 2.
- **Note 7:** Harmonics measured on the evaluation kit, which provides some harmonic attenuation in addition to the rejection provided by the IC. The combined suppression is specified.
- Note 8: ≥+25°C guaranteed by production test, ≤+25°C guaranteed through correlation to worst-case temperature testing.

Typical Operating Characteristics

(MAX2267/MAX2268/MAX2269 EV kits, V_{CC} = +3.5V, SHDN = V_{CC}, CDMA modulation, T_A = +25°C, unless otherwise noted.)

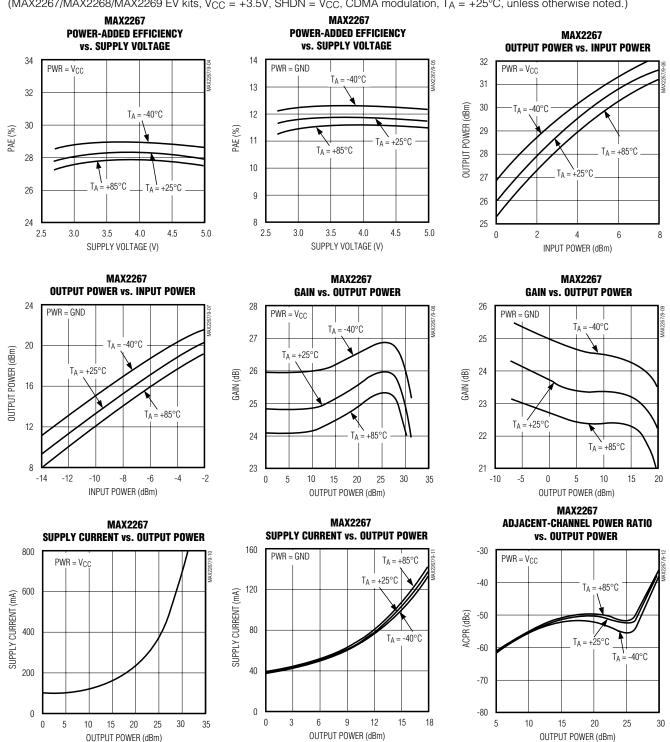






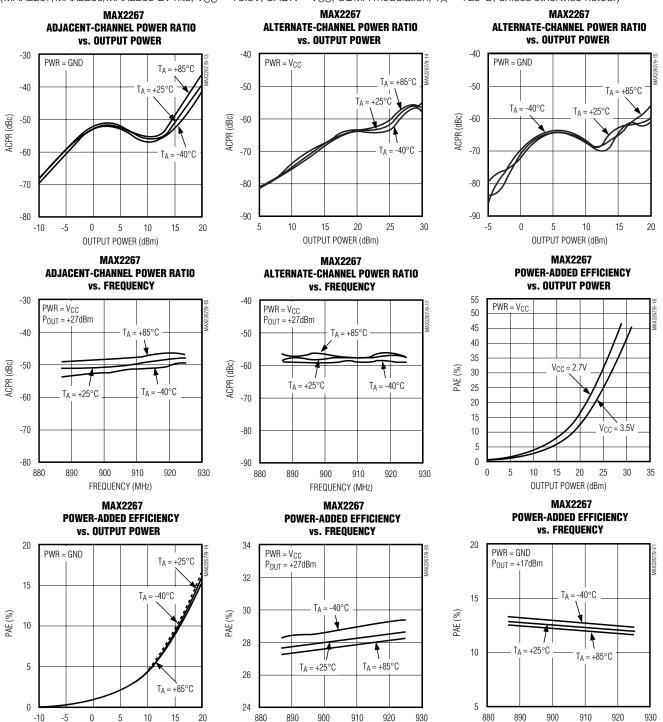
Typical Operating Characteristics (continued)

 $(MAX2267/MAX2268/MAX2269 EV kits, V_{CC} = +3.5V, \overline{SHDN} = V_{CC}, CDMA modulation, T_{A} = +25^{\circ}C, unless otherwise noted.)$



Typical Operating Characteristics (continued)

 $(\text{MAX2267/MAX2268/MAX2269} \text{ EV kits, V}_{\text{CC}} = +3.5\text{V}, \\ \overline{\text{SHDN}} = \text{V}_{\text{CC}}, \\ \text{CDMA modulation, T}_{\text{A}} = +25^{\circ}\text{C}, \\ \text{unless otherwise noted.})$



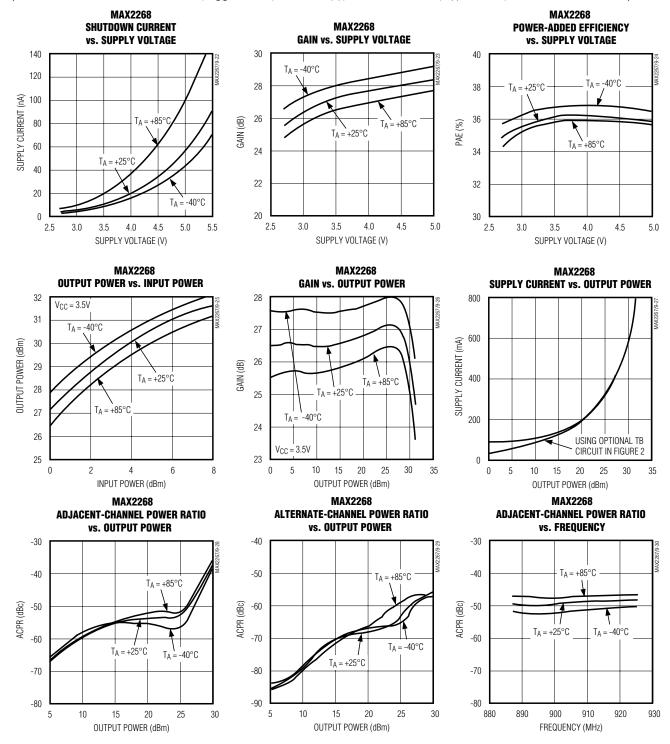
FREQUENCY (MHz)

OUTPUT POWER (dBm)

FREQUENCY (MHz)

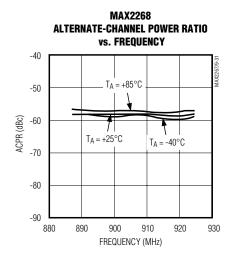
Typical Operating Characteristics (continued)

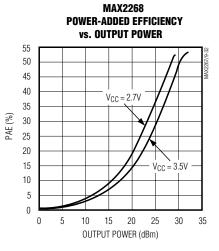
 $(MAX2267/MAX2268/MAX2269 EV kits, V_{CC} = +3.5V, \overline{SHDN} = V_{CC}, CDMA modulation, T_{A} = +25^{\circ}C, unless otherwise noted.)$

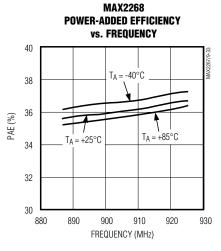


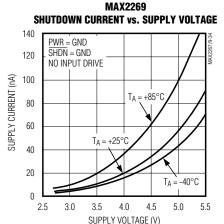
Typical Operating Characteristics (continued)

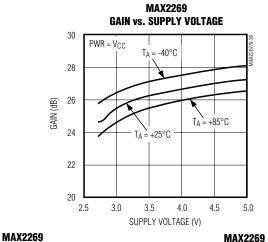
(MAX2267/MAX2268/MAX2269 EV kits, $V_{CC} = +3.5V$, $\overline{SHDN} = V_{CC}$, CDMA modulation, $T_A = +25^{\circ}C$, unless otherwise noted.)

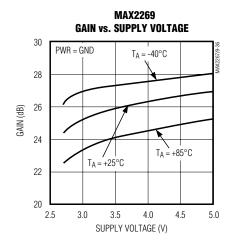


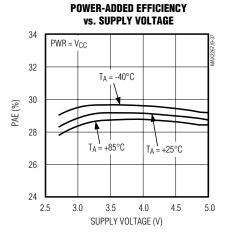


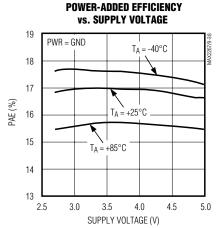






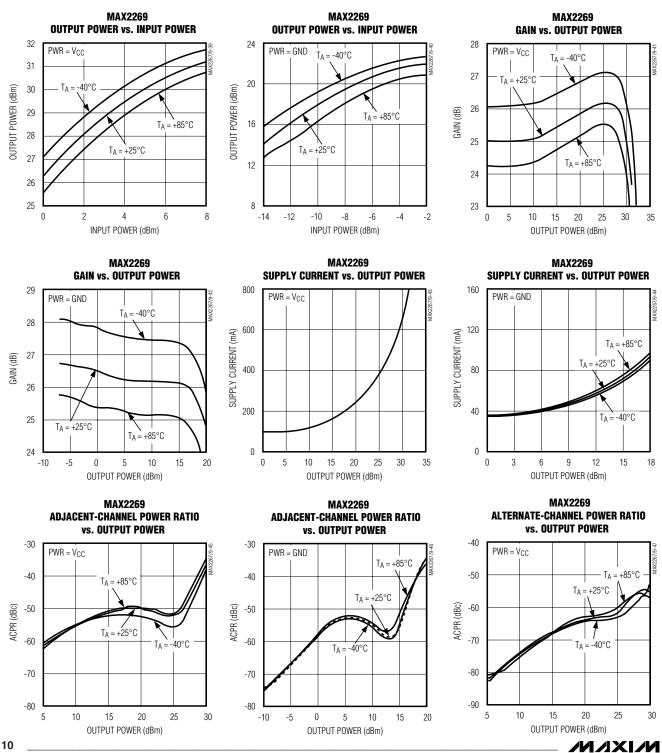






Typical Operating Characteristics (continued)

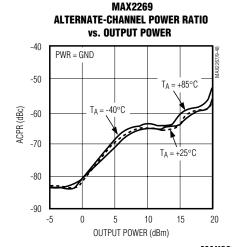
(MAX2267/MAX2268/MAX2269 EV kits, $V_{CC} = +3.5V$, $\overline{SHDN} = V_{CC}$, CDMA modulation, $T_A = +25^{\circ}C$, unless otherwise noted.)

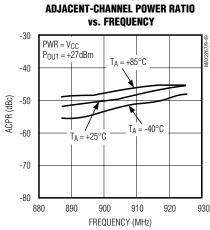


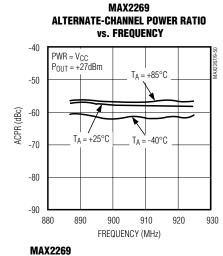
Typical Operating Characteristics (continued)

(MAX2267/MAX2268/MAX2269 EV kits, $V_{CC} = +3.5V$, $\overline{SHDN} = V_{CC}$, CDMA modulation, $T_A = +25^{\circ}C$, unless otherwise noted.)

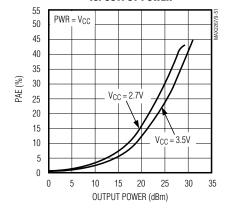
MAX2269



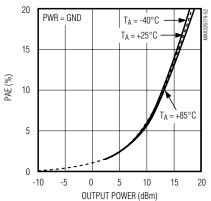




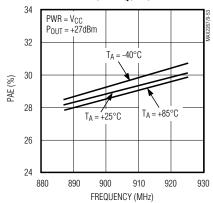
MAX2269
POWER-ADDED EFFICIENCY
vs. OUTPUT POWER



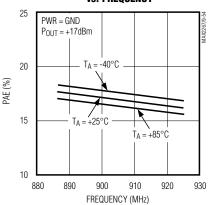
POWER-ADDED EFFICIENCY
vs. OUTPUT POWER



MAX2269
POWER-ADDED EFFICIENCY
vs. FREQUENCY



MAX2269
POWER-ADDED EFFICIENCY
vs. FREQUENCY



Pin Description

PIN			
MAX2267 MAX2269	MAX2268	NAME	FUNCTION
1	1	IN1	RF Input Port. Requires external matching network.
2	_	PWR	Mode-Select Input. Drive low to select the low-power mode (BIAS1L and BIAS2L). Drive high to select high-power mode (BIAS1H and BIAS2H).
3, 5, 14	3, 5	V _{CC}	Voltage Supply. It is critical to bypass these pins with capacitors to GND as close to the pins as possible.
4	4	BIAS1H	High-Power Mode First Stage Bias Control. See General Description.
6	2, 6	SHDN	Shutdown Control Input. Drive SHDN low to enable shutdown. Drive high for normal operation. On the MAX2268, make sure that both pins get driven simultaneously. To place the MAX2267 into shutdown mode, also pull the PWR pin low.
7	_	BIAS2L	Low-Power Mode Second Stage Bias Control. See General Description.
8, 9	8, 9	OUT1	RF Output Ports. Require an appropriate output matching network and collector bias.
10	_	BIAS1L	Low-Power Mode First Stage Bias Control. See General Description.
11	_	OUT0	RF Output Port. Requires an appropriate output matching network and collector bias.
12	12	NFP	Noise Filtering Pin. Connect noise filtering network as described in Noise Filtering section. If unused, leave open.
_	7, 10, 11, 14, 16	N.C.	Not internally connected. Do not make any connections to these pins.
13, Slug	13, Slug	GND	Ground. Solder the package slug to high-thermal-conductivity circuit board ground plane.
15	15	BIAS2H	High-Power Mode Second Stage Bias Control. See General Description.
16	_	IN0	RF Input Port. Requires external matching network.

Detailed Description

The MAX2267/MAX2268/MAX2269 are linear power amplifiers (PAs) intended for CDMA and TDMA applications. The devices have been fully characterized in the 887MHz to 925MHz Japanese cellular band and can be used from 750MHz to 1000MHz by adjusting the input and output match. In CDMA applications, they provide +27dBm of output power and up to 35% power-added efficiency (PAE) from a single +2.7V to +4.5V supply.

An inherent drawback of traditional PAs is that their efficiency drops rapidly with reduced output power. For example, in a PA designed for maximum efficiency at +27dBm, the efficiency at +15dBm falls well below 4.5% (over 200mA from a 3.5V supply). This behavior significantly reduces talk time in CDMA phones because over 90% of the time they are at output powers below +16dBm. The MAX2267/MAX2268/MAX2269

are optimized for lowest current draw at output powers that are most likely to occur in real-life situations. This provides up to 50% reduced average PA current.

High-Power and Low-Power Modes

The MAX2267/MAX2269 are designed to provide optimum PAE in both high- and low-power modes. For a +3.5V supply, maximum output power is +27dBm in high-power mode. In low-power mode, output power is +17dBm and +17.5dBm, respectively. Use the system's microcontroller to determine required output power, and switch between the two modes as appropriate with the PWR logic pin.

Bias Control

The bias current of the first stage in low-power mode is proportional to the current flowing out of BIAS1L. The voltage at BIAS1L is fixed by an internal bandgap refer-

ence, so the current out of this pin is inversely proportional to the value of the resistor between this pin and ground. Similarly, the bias current of the first stage in high-power mode is proportional to the current flowing out of BIAS1H. The current in the second stage is proportional to the currents out of BIAS2L and BIAS2H for low- and high-power modes, respectively.

Additionally, these resistors allow for customization of gain and alternate- and adjacent-channel power ratios. Increasing the bias current in the first stage increases the gain and improves alternate-channel power ratio at the expense of efficiency. Increasing the bias current in the second stage increases gain at the expense of efficiency as well as adjacent- and alternate-channel power ratios.

The PA bias current can be dynamically adjusted by summing a current into the bias pin of interest with an external source such as a DAC. See the MAX2268 *Typical Application Circuit* for using a voltage DAC and current setting resistors RTB1 and RTB2. Choosing RTB1 = R1 and RTB2 = R2 allows current adjustment between 0mA to double the nominal idle current with

DAC voltages between 0V and 2.4V. The DAC must be able to source approximately 100uA.

Shutdown Mode

Pull pins 2 and 6 low to place the MAX2267/MAX2268/MAX2269 into shutdown mode. In this mode, all gain stages are disabled and supply current drops to 0.5µA.

Applications Information

Increasing Efficiency

The MAX2269 incorporates an additional external switch to increase efficiency to 17% at +17dBm and to 29% at +27dBm. This increase in efficiency is mainly due to the additional isolation between the high- and low-power outputs provided by the external switch.

External Components

The MAX2267/MAX2268/MAX2269 require matching circuits at their inputs and outputs for operation in a 50Ω system. The simplified application circuits in Figures 1, 2, and 3 describe the topology of the circuit-

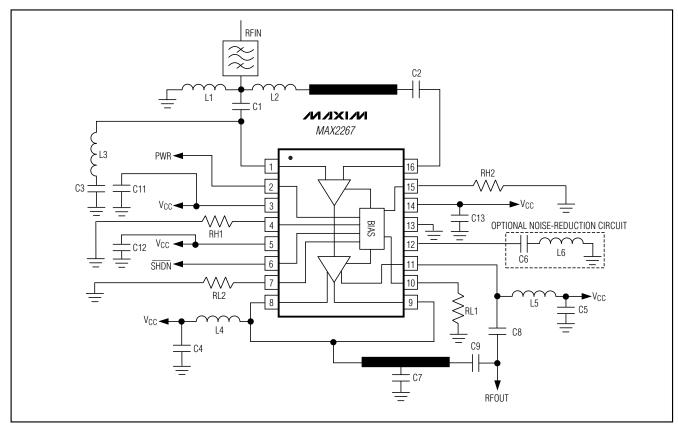


Figure 1. MAX2267 Typical Application Circuit

ry for each device. For more detailed circuit diagrams, refer to the MAX2267/MAX2268/MAX2269 EV kit manual. The EV kit manual suggests component values that are optimized for best simultaneous efficiency and return loss performance. Use high-quality components in these matching circuits for greatest efficiency.

Layout and Power-Supply Bypassing

A properly designed PC board is essential to any RF/microwave circuit. Be sure to use controlled impedance lines on all high-frequency inputs and outputs. Proper grounding of the GND pins is fundamental; if the PC board uses a topside RF ground, connect all GND pins (especially the TSSOP package exposed GND pad) directly to it. On boards where the ground plane is not on the component side, it's best to connect all GND pins to the ground plane with plated through-holes close to the package.

To minimize coupling between different sections of the system, the ideal power-supply layout is a star configuration with a large decoupling capacitor at a central VCC node. The VCC traces branch out from this central node, each leading to a separate VCC node on the PC board. A second bypass capacitor with low ESR at the RF frequency of operation is located at the end of each trace. This arrangement provides local decoupling at the VCC pin.

Input and output impedance-matching networks are very sensitive to layout-related parasitics. It is important to keep all matching components as close to the IC as possible to minimize the effects of stray inductance and stray capacitance of PC board traces.

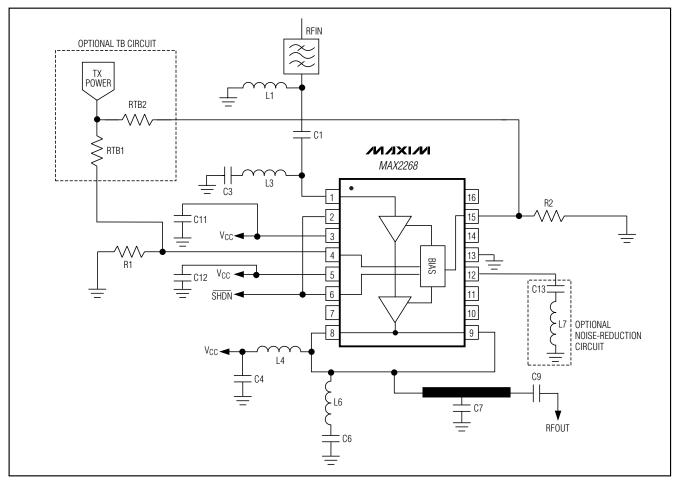


Figure 2. MAX2268 Typical Application Circuit

Noise Filtering

For improved noise performance, the MAX2267/MAX2268/MAX2269 allow for additional noise filtering for further suppression of transmit noise. Use the rec-

ommended component values in the MAX2267/MAX2268/MAX2269 EV kit manual for optimal noise power.

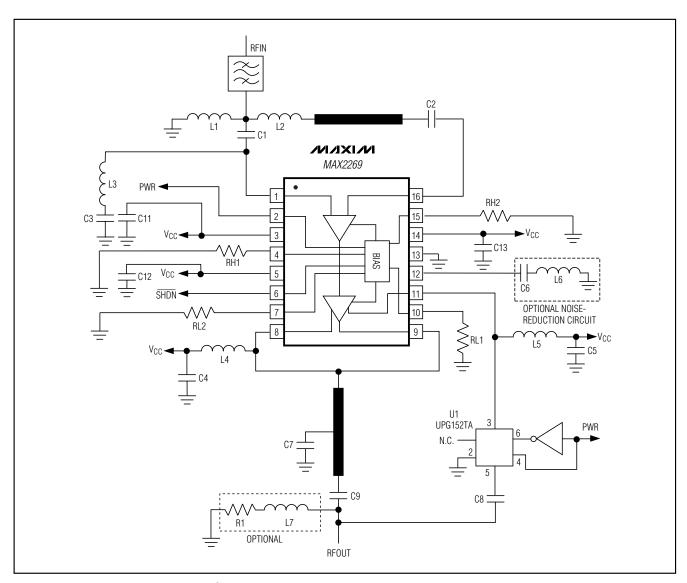
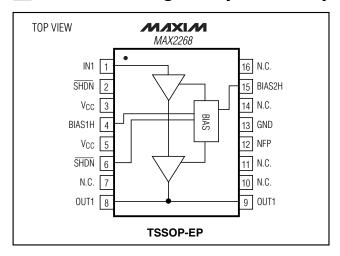


Figure 3. MAX2269 Typical Application Circuit

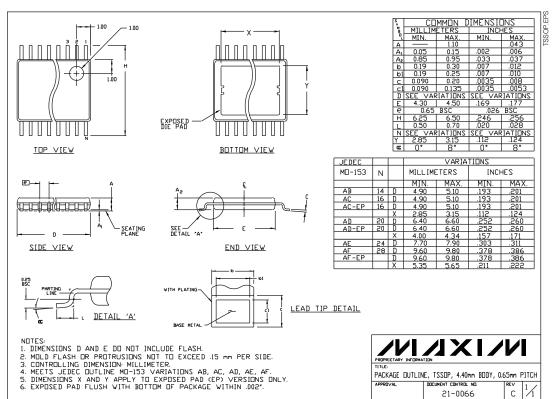
Pin Configurations/ Functional Diagrams (continued)

Chip Information

TRANSISTOR COUNT: 1256



Package Information



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